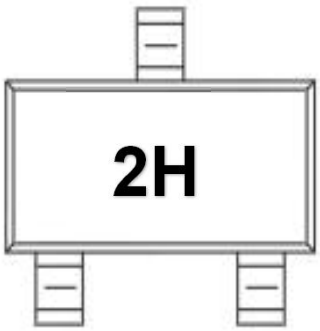
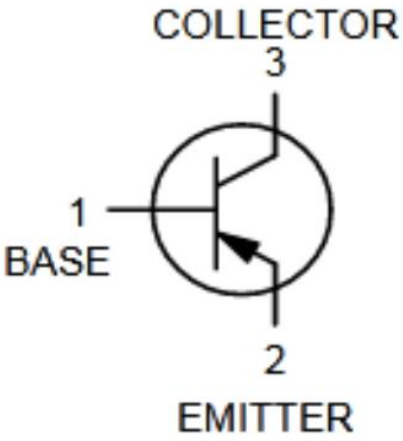
TRANSI STOR (PNP)

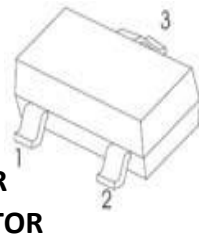
MARKING:



Equivalent Circuit:



SOT-23



1.BASE
2.EMITTER
3.COLLECTOR

FEATURES:

※ Collector Current Capability IC=-0.5A
※ Collector Emitter Voltage VCEO=-60V

MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

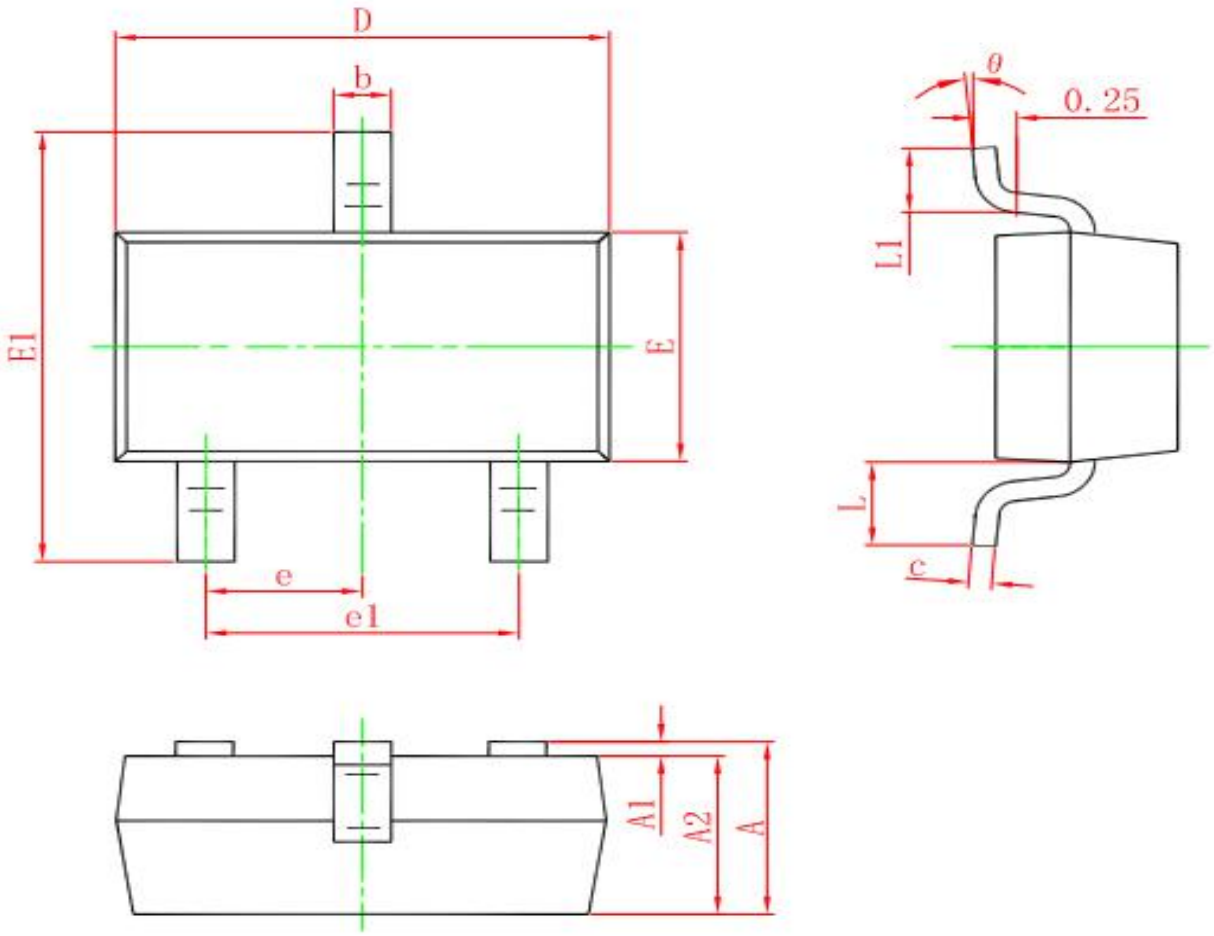
Parameter	Symbol	Value	Unit
Collector-Base Voltage	**VCBO**	-60	**V**
Collector-Emitter Voltage	**VCEO**	-60	**V**
Emitter-Base Voltage	**VEBO**	-4	**V**
Collector Current	**IC**	-500	**mA**
Collector Power Dissipation	**PC**	225	**mW**
Thermal Resistance From Junction To Ambient	**RΘJA**	556	**℃/W**
Junction Temperature	**Tj**	150	**℃**
Storage Temperature	**Tstg**	-55～+150	**℃**

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	**V(BR)CBO**	IC= -100μA, IE=0	-60			**V**
Collector-emitter breakdown voltage	**V(BR)CEO**	IC= -1mA, IB=0	-60			**V**
Emitter-base breakdown voltage	**V(BR)EBO**	IE=-100μA, IC=0	-4			**V**
Collector cut-off current	**ICBO**	VCB=-60 V , IE=0			-0.1	**μA**
Collector cut-off current	**ICEO**	VCB=-60V , IE=0			-1	**μA**
Emitter cut-off current	**IEBO**	VEB= -4V , IC=0			-0.1	**μA**
DC current gain	**hFE**	VCE=-1V, IC= -10mA	100		400	
	hFE	VCE=-1V, IC= -100mA	100			
Collector-emitter saturation voltage	**VCE(sat)**	IC=-100 mA, IB= -10mA			-0.25	**V**
Base-emitter saturation voltage	**VBE(sat)**	VCE=-1V, IC=-100mA			-1.2	**V**
Transition frequency	**fT**	VCE=-1V, IC= -100mA f=100MHz	50			**MHz**

Note. Pulse Test: Pulse Width ≤300 us, Duty Cycle ≤2.0%

SOT-23 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°